14 W × 4-Channel BTL Power IC

HITACHI

ADE-207-116 1st. Edition

Description

The HA13151/HA13152 are high output and low distortion 4 ch BTL power IC designed for digital car audio.

At 13.2 V to 4 load, this power IC provides output power 14 W with 10% distortion.

Functions

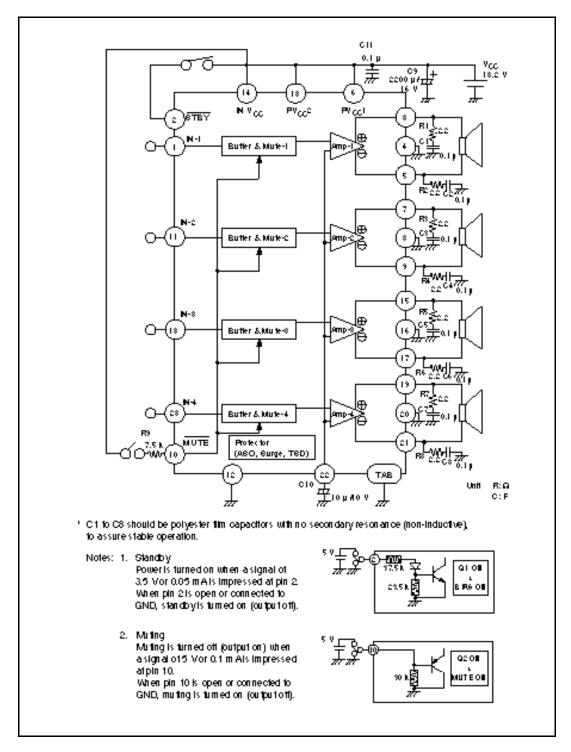
- 4 ch BTL power amplifiers
- · Built-in standby circuit
- · Built-in muting circuit
- Built-in protection circuit (surge, T.S.D, and ASO)

Features

- · Few external parts lead to compact set-area possibility
- · Popping noise minimized
- · Low output noise
- · Built-in high reliability protection circuit



Block Diagram



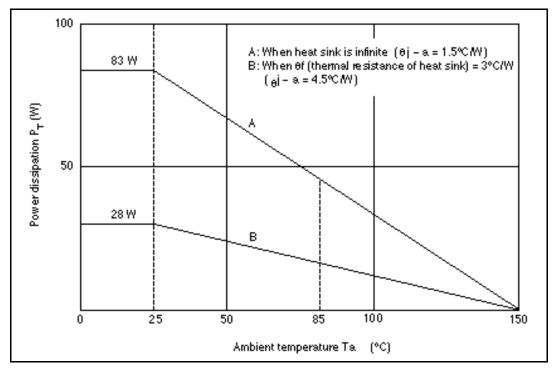
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item Symbol Rating Unit Remarks

			HA13151, HA13152
Operating supply voltage	V_{cc}	18	V
Supply voltage when no signal*1	V _{cc} (DC)	26	V
Peak supply voltage*2	V _{cc} (PEAK)	50	V
Output current*3	I _o (PEAK)	3	Α
Power dissipation*4	P _T	83	W
Junction temperature	Tj	150	°C
Operating temperature	Topr	-30 to +85	°C
Storage temperature	Tstg	-55 to +125	°C

Notes: 1. Tolerance within 30 seconds

- 2. Tolerance in surge pulse waveform
- 3. Value per 1 channel
- 4. Value when attached on the infinite heat sink plate at Ta = 25 °C. The derating carve is as shown in the graph below.



Electrical Characteristics (V $_{CC}$ = 13.2 V, $\,f$ = 1 kHz, $\,R_L$ = 4 $\,$, $\,Rg$ = 600 $\,$, $\,Ta$ = 25°C)

HA13151

Quiescent current I _Q 1 Output offset voltage V Gain Gain G _V Gain difference between channels		 -300 30.5 -1.5	270 0 32 0	+300 33.5	mA mV dB	Vin = 0
Gain G _v Gain difference between channels		30.5	32	33.5		
Gain difference between Gchannels	v				dB	
channels	V	-1.5	0			
				+1.5	dB	
Rated output power Po		_	14	_	W	$V_{CC} = 13.2 \text{ V}$ THD = 10%, $R_L = 4$
Max output power Por	max	_	22	_	W	$V_{CC} = 13.7 \text{ V}$ THD = Max, $R_L = 4$
Total harmonic distortion T.F	I.D.	_	0.05	_	%	Po = 3 W
Output noise voltage WE	BN	_	0.15	_	mVrms	Rg = 0 BW = 20 to 20 kHz
Ripple rejection SV	R	_	55	_	dB	Rg = 600 , f = 120 Hz
Channel cross talk C.1		_	70	_	dB	Rg = 600 Vout = 0 dBm
Input impedance Rin		_	25	_	k	
Standby current I _Q 2		_	_	200	μΑ	
Standby control voltage V _{ST} (high)	Н	3.5	_	V _{cc}	V	
Standby control voltage V _{ST} (low)	L	0	_	1.5	V	
Muting control voltage V _{MH} (high)	ł	3.5	_	V _{cc}	V	
Muting control voltage V _{ML} (low)		0	_	1.5	V	
Muting attenuation AT	TM	_	70	_	dB	Vout = 0 dBm

HA13152

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Quiescent current	I _Q 1	_	270	_	mA	Vin = 0
Output offset voltage	V _Q	-300	0	+300	mV	
Gain	G _v	38.5	40	41.5	dB	
Gain difference between channels	G_{v}	-1.5	0	+1.5	dB	
Rated output power	Po	_	14	_	W	V _{cc} = 13.2 V THD = 10%, R _L = 4
Max output power	Pomax	_	22	_	W	$V_{CC} = 13.7 \text{ V}$ THD = Max, $R_L = 4$
Total harmonic distortion	T.H.D.	_	0.05	_	%	Po = 3%
Output noise voltage	WBN	_	0.25	_	mVrms	Rg = 0 BW = 20 to 20 kHz
Ripple rejection	SVR		45		dB	Rg = 600 , f = 120 Hz
Channel cross talk	C.T.	_	60	_	dB	Rg = 600 Vout = 0 dBm
Input impedance	Rin	_	25	_	k	
Standby current	I _Q 2		_	200	μA	
Standby control voltage (high)	V_{STH}	3.5	_	V _{cc}	V	
Standby control voltage (low)	V_{STL}	0	_	1.5	V	
Muting control voltage (high)	V_{MH}	3.5		V _{cc}	V	
Muting control voltage (low)	V_{ML}	0		1.5	V	
Muting attenuation	ATTM		60		dB	Vout = 0 dBm

Pin Explanation

Pin No.	Symbol	Functions	Input Impedance	DC Voltage	Equivalence Circuit
1	IN1	CH1 INPUT	25 k (Typ)	0 V	1
11	IN2	CH2 INPUT	<u></u>		
13	IN3	CH3 INPUT	_		
23	IN4	CH4 INPUT			
2	STBY	Standby control	90 k (at Trs. cutoff)	_	23.5 k
3	OUT1 +	CH1 OUTPUT		V _{co} /2	3
5	OUT1 –				
7	OUT2 +	CH2 OUTPUT			
9	OUT2 -		<u> </u>		
15	OUT3 +	CH3 OUTPUT			
17	OUT3 -		_		
19	OUT4 +	CH4 OUTPUT			
21	OUT4 –				
10	MUTE	Muting control	25 k (Typ)	_	10 € 25 k

Pin Explanation (cont)

Pin No.	Symbol	Functions	Input Impedance	DC Voltage	Equivalence Circuit
22	RIPPLE	Bias stability	_	V _{cc} /2	**************************************
6	PV _{cc} 1	Power of output stage	_	V _{cc}	_
18	PV _{cc} 2				
14	INV _{cc}	Power of input stage	_	V_{cc}	_
4	CH1 GND	CH1 power GND	_	_	_
8	CH2 GND	CH2 power GND	_		
16	CH3 GND	CH3 power GND	_		
20	CH4 GND	CH4 power GND	_		
12	IN GND	Input signal GND	_	_	_

Point of Application Board Design

- 1. Notes on Application Board's Pattern Design
- For increasing stability, the connected line of V_{CC} and OUTGND is better to be made wider and lower impedance.
- For increasing stability, it is better to place the capacitor between V_{CC} and GND (0.1 μF) close to IC.
- For increasing stability, it is better to place C1 to C8 and R1 to R8, which are for stopping oscillation, close to IC.
- It is better to place the grounding of resistor (Rg), between input line and ground, close to INGND
 (Pin 12) because if OUTGND is connected to the line between Rg and INGND, THD will become
 worse due to current from OUTGND.

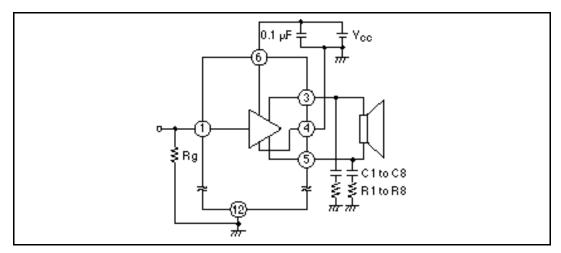


Figure 1 Notes on Application Board's Pattern Design

2. How to Reduce the Popping Noise by Muting Circuit

At normal operating circuit, Muting circuit operates at high speed under 1 µs.

In case popping noise becomes a problem, it is possible to reduce the popping noise by connecting capacitor, which determines the switching time constant, between pin 10 and GND. (Following figure 2)

We recommend value of capacitor greater then 1 µF.

Also transitional popping noise can be reduced sharply by muting before V_{CC} and Standby are ON/OFF.

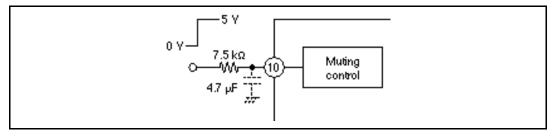
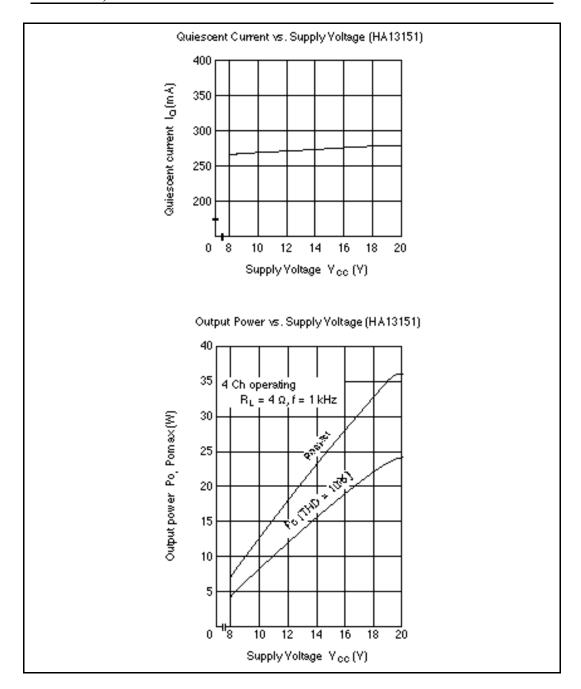
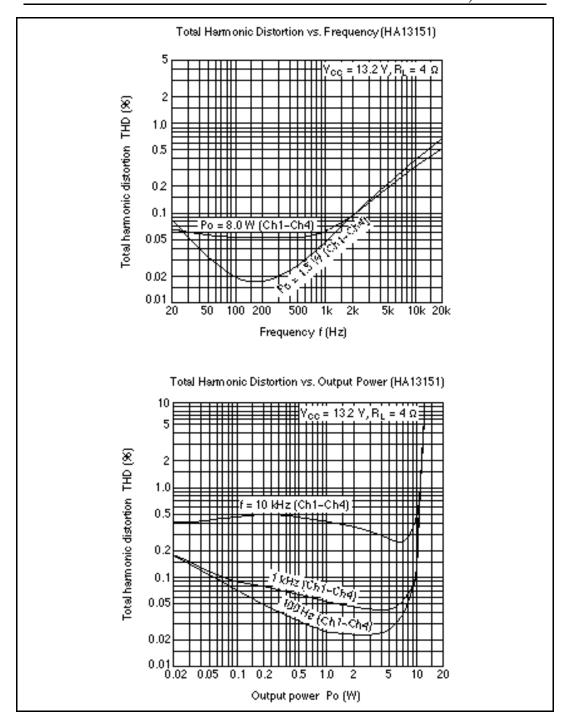


Figure 2 How to use Muting Circuit

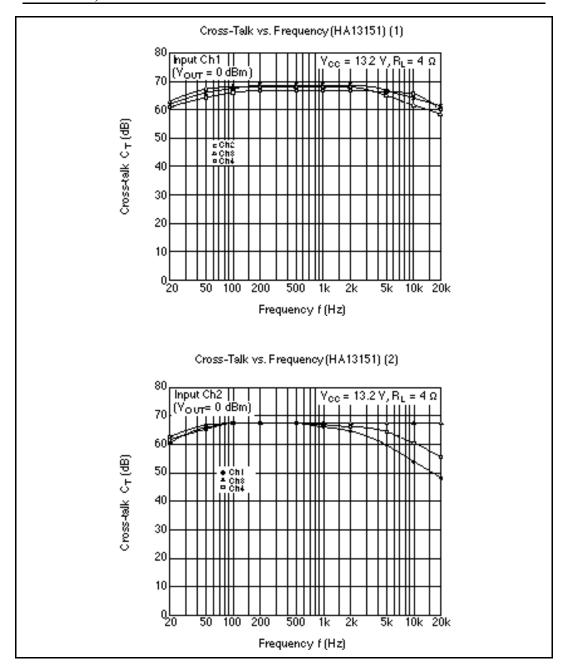
Table 1 Muting ON/OFF Time

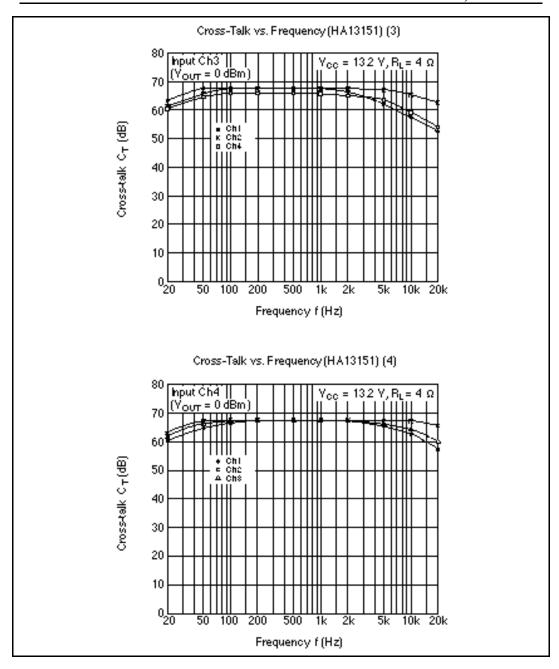
C (µF)	ON Time	OFF Time
nothing	under 1 µs	under 1 µs
0.47	2 ms	2 ms
4.7	19 ms	19 ms

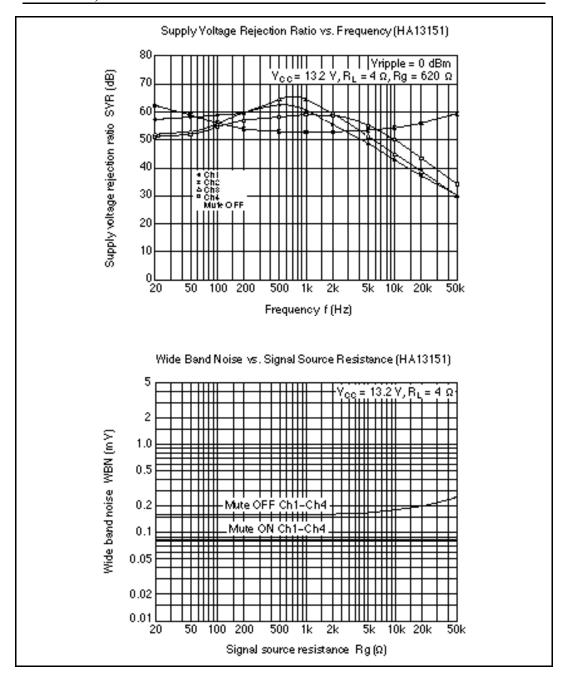


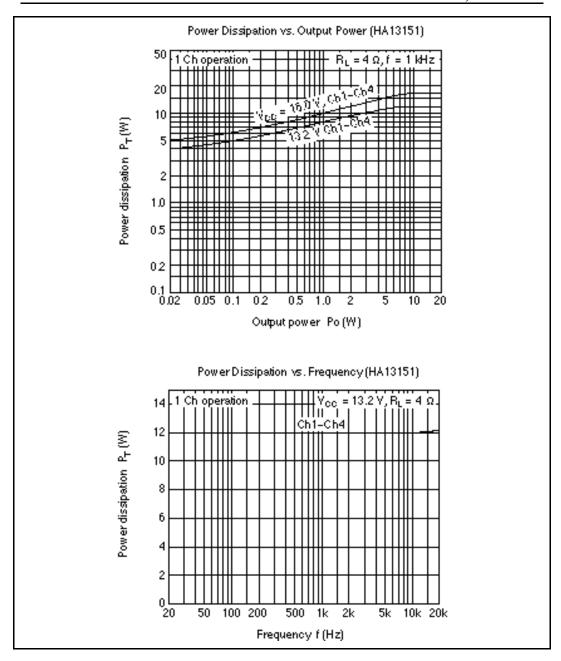


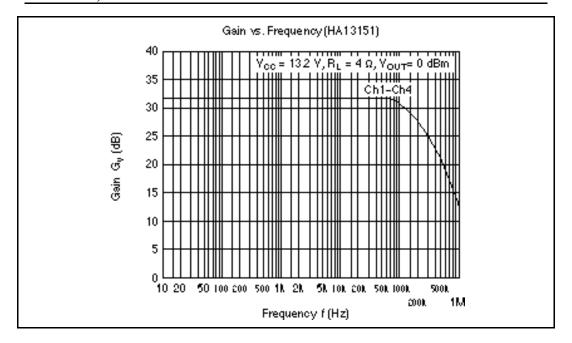
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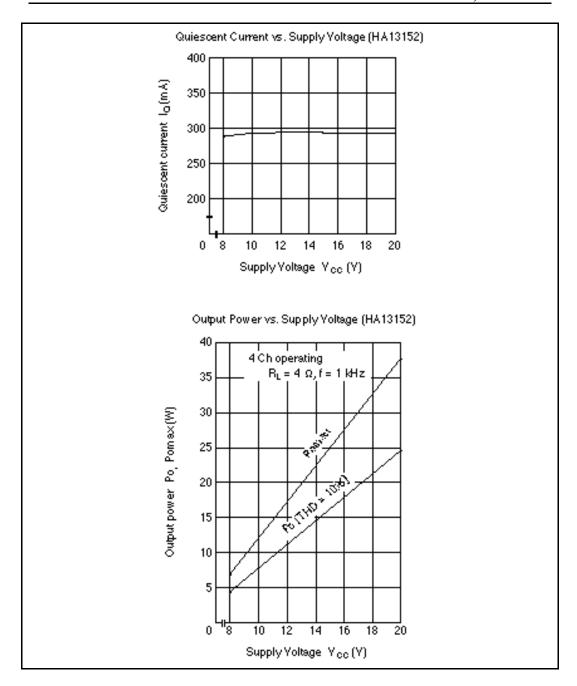


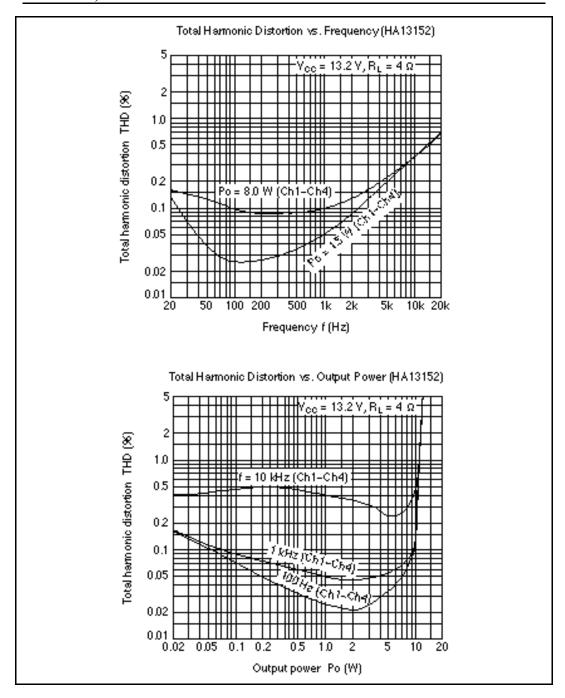


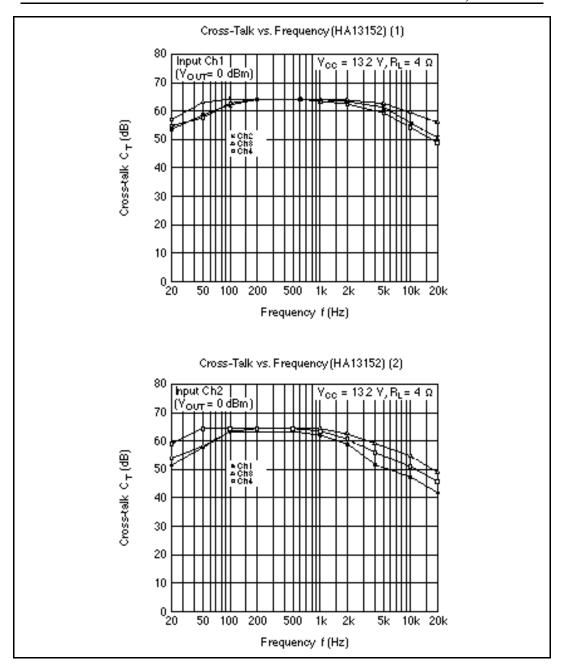


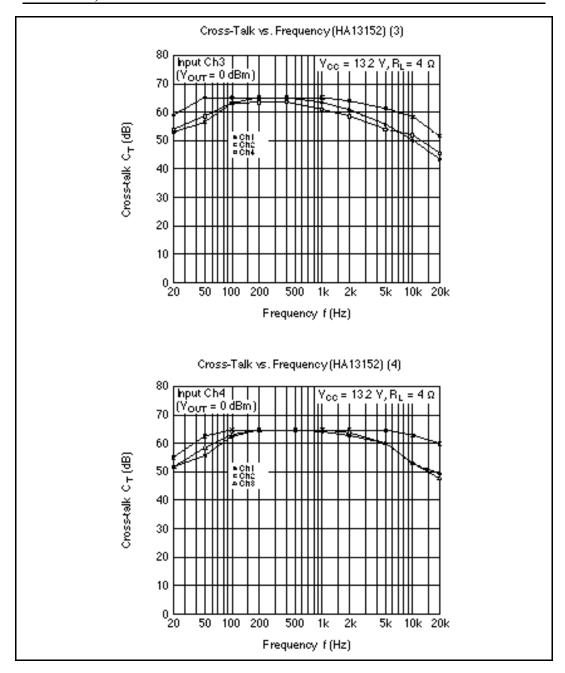


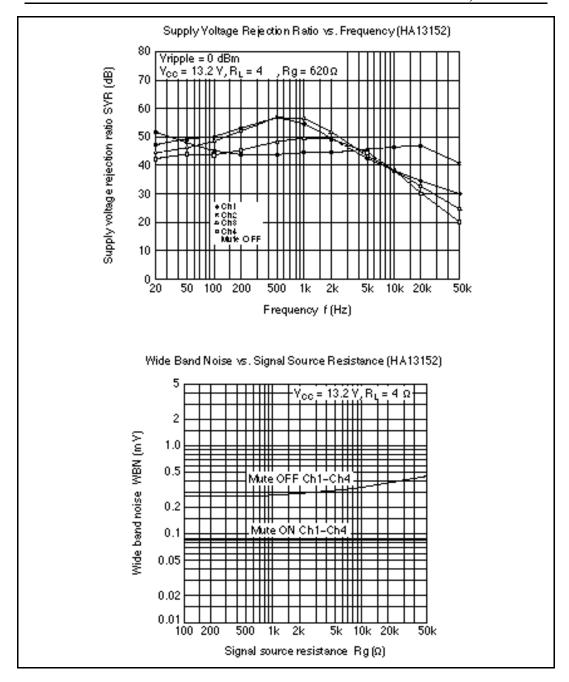


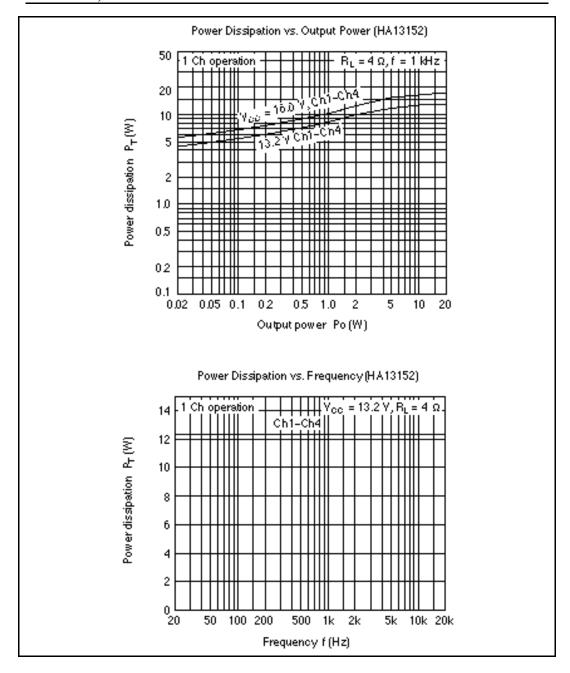


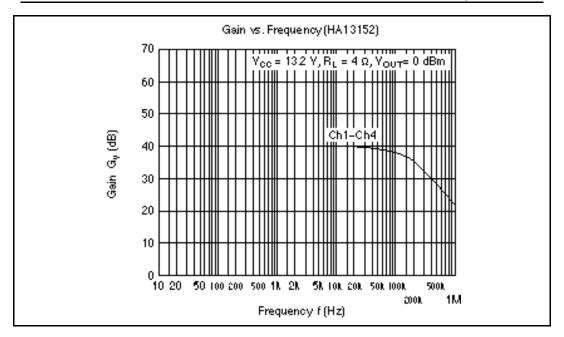












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